

# **STTH30R04**

## Ultrafast recovery diode

### Main product characteristics

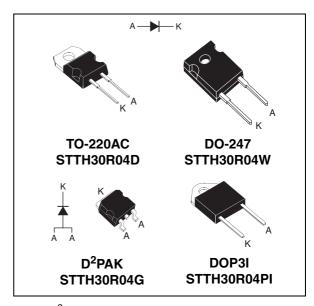
I <sub>F(AV)</sub>	30 A
V <sub>RRM</sub>	400 V
T <sub>j</sub>	175° C
V <sub>F</sub> (typ)	0.97 V
t <sub>rr</sub>	24 ns

### Features and benefits

- Ultrafast switching
- Low reverse current
- Low thermal resistance
- Reduces switching and conduction losses
- High junction temperature
- Insulated package: DOP3I
  - Electrical insulation = 2500 V<sub>RMS</sub>
    Package capacitance = 12 pF

## **Description**

The compromise-free, high quality design of this diode has produced a device with low leakage current, regularly reproducible characteristics and intrinsic ruggedness. These characteristics make it ideal for heavy duty applications that demand long term reliability.



Note: D<sup>2</sup>PAK - 2 anode terminals must be shorted on board.

### **Order codes**

Part Number	Marking
STTH30R04D	STTH30R04D
STTH30R04G	STTH30R04G
STTH30R04G-TR	STTH30R04G
STTH30R04W	STTH30R04W
STTH30R04PI	STTH30R04PI

Table 1. Absolute ratings (limiting values at 25° C, unless otherwise specified)

Symbol	F		Value	Unit	
V <sub>RRM</sub>	Repetitive peak reverse voltage	Repetitive peak reverse voltage			
I <sub>F(RMS)</sub>	RMS forward current			50	Α
1	Average forward current, $\delta = 0.5$	TO-220AC / DO-247 / D <sup>2</sup> PAK	T <sub>c</sub> = 120° C	30	Α
Average forward current,	Average forward current, $\delta = 0.5$	DOP3I	T <sub>c</sub> = 90° C	30	^
I <sub>FRM</sub>	Repetitive peak forward current $t_p = 10 \mu s$ , $F = 1 kHz$		500	Α	
I <sub>FSM</sub>	Surge non repetitive forward current $t_p = 10 \text{ ms Sinusoidal}$			300	Α
T <sub>stg</sub>	Storage temperature range			-65 to +175	° C
T <sub>j</sub>	Maximum operating junction temperature range			-40 to +175	° C

**Characteristics STTH30R04** 

#### **Characteristics** 1

Table 2. Thermal parameters

Symbol	Parameter V			Unit
R <sub>th(j-c)</sub> Junction to case		TO-220AC / DO-247 / D <sup>2</sup> PAK	1.15	°C/W
	DOP3I	1.9	C/VV	

Static electrical characteristics Table 3.

Symbol	Parameter	Test conditions		Min	Тур	Max	Unit
		T <sub>j</sub> = 25° C				15	
I <sub>R</sub> <sup>(1)</sup>	I <sub>R</sub> <sup>(1)</sup> Reverse leakage current	T <sub>j</sub> = 100° C	$V_R = V_{RRM}$		3	30	μΑ
		T <sub>j</sub> = 125° C			15	150	
	V <sub>F</sub> <sup>(2)</sup> Forward voltage drop	T <sub>j</sub> = 25° C	I <sub>F</sub> = 15 A			1.26	
		T <sub>j</sub> = 150° C	1F = 13 A		0.8	1.0	
V <sub>F</sub> <sup>(2)</sup>		T <sub>j</sub> = 25° C				1.45	V
	T <sub>j</sub> = 100° C	I <sub>F</sub> = 30 A			1.3		
		T <sub>j</sub> = 150° C			0.97	1.2	

<sup>1.</sup> Pulse test:  $t_p = 5$  ms,  $\delta < 2$  %

To evaluate the conduction losses use the following equation: P = 0.9 x  $I_{F(AV)}$  + 0.01 x  $I_{F}^{2}_{(RMS)}$ 

$$P = 0.9 \text{ x } I_{F(AV)} + 0.01 \text{ x } I_{F}^{2}_{(RMS)}$$

Table 4. **Dynamic characteristics** 

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
		$I_F = 1 \text{ A, } dI_F/dt = -200 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25^{\circ} \text{ C}$		24	35	
t <sub>rr</sub>	t <sub>rr</sub> Reverse recovery time	$I_F = 1 \text{ A, } dI_F/dt = -15 \text{ A/}\mu\text{s,}$ $V_R = 30 \text{ V, } T_j = 25^{\circ} \text{ C}$		78	100	ns
		$I_F = 1 \text{ A}, I_R = 1 \text{ A},$ $I_{RR} = 0.25 \text{ A}, T_j = 25^{\circ} \text{ C}$			50	
I <sub>RM</sub>	Reverse recovery current	$I_F = 30 \text{ A}, dI_F/dt = -200 \text{ A/µs},$ $V_R = 160 \text{ V}, T_j = 125^{\circ} \text{ C}$		10	14	Α
t <sub>fr</sub>	Forward recovery time	$I_F = 30 \text{ A}$ $dI_F/dt = 100 \text{ A/}\mu\text{S}$ $V_{FR} = 1.1 \text{ x } V_{Fmax}, T_j = 25^{\circ} \text{ C}$			500	ns
V <sub>FP</sub>	Forward recovery voltage	$I_F = 30 \text{ A}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$ $V_{FR} = 1.1 \text{ x } V_{Fmax}, T_j = 25^{\circ} \text{ C}$		2.9		٧

<sup>2.</sup> Pulse test:  $t_p$  = 380  $\mu$ s,  $\delta$  < 2 %

STTH30R04 Characteristics

Figure 1. Conduction losses versus average current

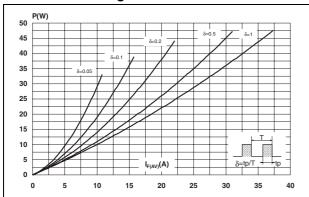


Figure 2. Forward voltage drop versus forward current

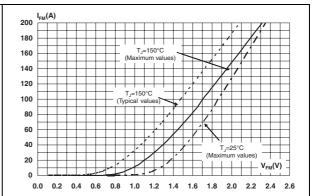
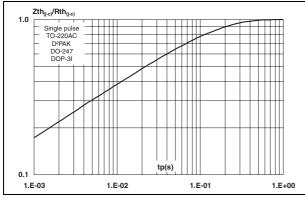


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Peak reverse recovery current versus dl<sub>F</sub>/dt (typical values)



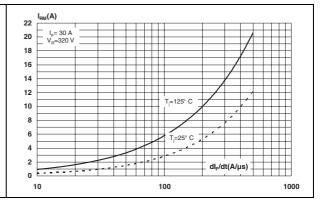


Figure 5. Reverse recovery time versus dl<sub>F</sub>/dt (typical values)

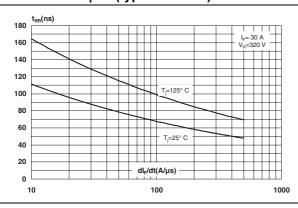
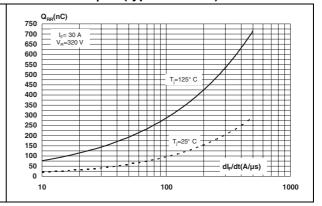


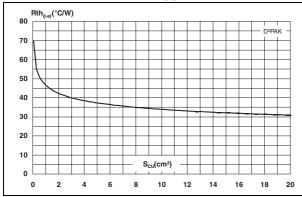
Figure 6. Reverse recovery charges versus dl<sub>F</sub>/dt (typical values)



Characteristics STTH30R04

Figure 7. Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4,  $e_{CU} = 35 \mu m$ )

Figure 8. Relative variations of dynamic parameters versus junction temperature



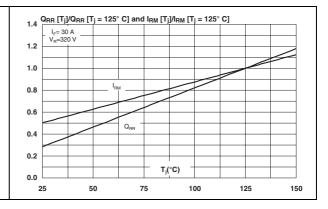
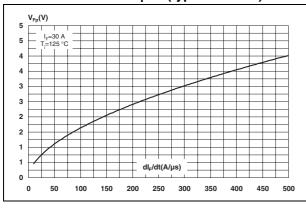


Figure 9. Transient peak forward voltage versus dl<sub>F</sub>/dt (typical values)

Figure 10. Forward recovery time versus dI<sub>F</sub>/dt (typical values)



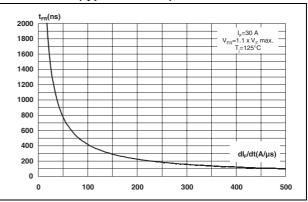
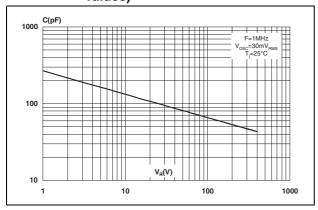


Figure 11. Junction capacitance versus reverse voltage applied (typical values)



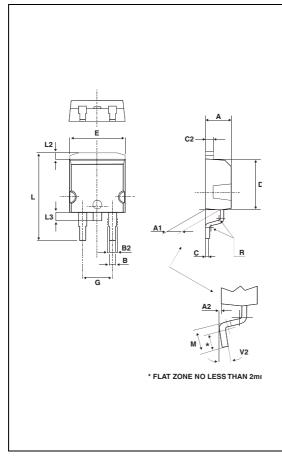
577

STTH30R04 Package information

# 2 Package information

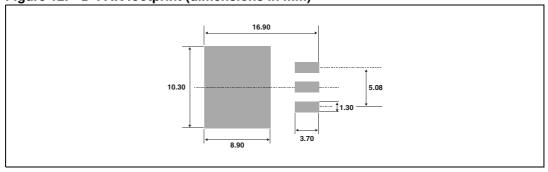
- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.8 Nm (TO-220FPAC) / 0.55 Nm (TO-220AC, DOP3I)
- Maximum torque value: 1.0 Nm (TO-220FPAC) / 0.70 Nm (TO-220AC, DOP31)

Table 5. D<sup>2</sup>PAK dimensions



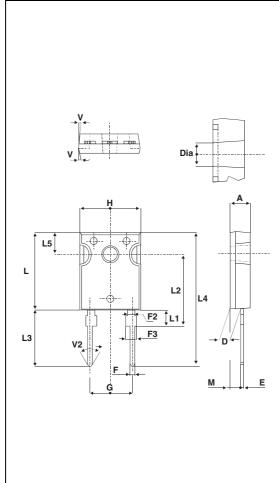
		Dimer	nsions	
Ref.	Millim	neters	Inc	hes
	Min.	Max.	Min.	Max.
Α	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
В	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
С	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
Е	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.40	1.75	0.055	0.069
М	2.40	3.20	0.094	0.126
R	0.40	typ.	0.016	3 typ.
V2	0°	8°	0°	8°

Figure 12. D<sup>2</sup>PAK footprint (dimensions in mm)



Package information STTH30R04

Table 6. DO-247 dimensions



			Dimer	nsions		
Ref.	Millimete		ers	Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	4.85		5.15	0.191		0.203
D	2.20		2.60	0.086		0.102
Е	0.40		0.80	0.015		0.031
F	1.00		1.40	0.039		0.055
F2		2.00			0.078	
F3	2.00		2.40	0.078		0.094
G		10.90			0.429	
Н	15.45		15.75	0.608		0.620
L	19.85		20.15	0.781		0.793
L1	3.70		4.30	0.145		0.169
L2		18.50			0.728	
L3	14.20		14.80	0.559		0.582
L4		34.60			1.362	
L5		5.50			0.216	
М	2.00		3.00	0.078		0.118
V		5°			5°	
V2		60°			60°	
Dia.	3.55		3.65	0.139		0.143

6/10

**STTH30R04 Package information** 

Max.

0.181

0.051

0.107

0.027

0.034

0.066

0.202

0.409

0.551

0.116

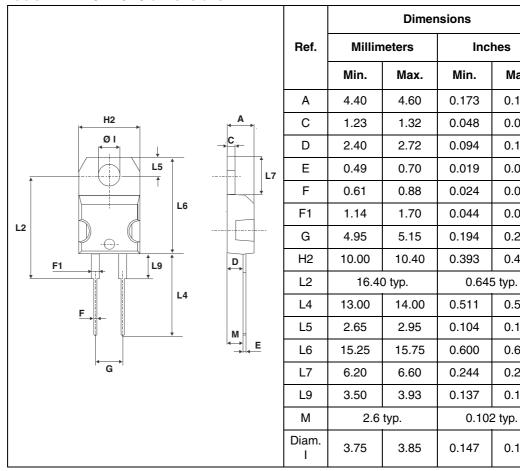
0.620

0.259

0.154

0.151

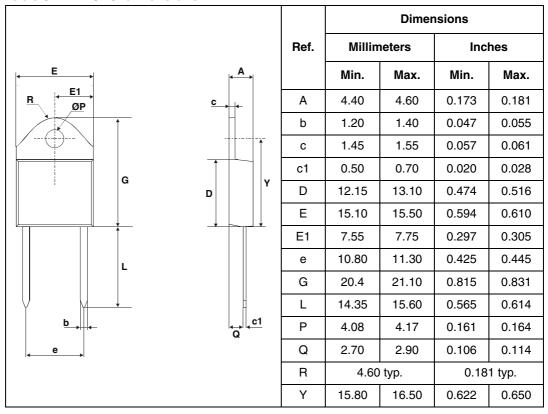
**TO-220AC dimensions** Table 7.



7/10

Package information STTH30R04

Table 8. DOP3I dimensions



In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

# 3 Ordering information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
STTH30R04D	STTH30R04D	TO-220AC	1.86 g	50	Tube
STTH30R04G	STTH30R04G	D <sup>2</sup> PAK	1.48 g	50	Tube
STTH30R04G-TR	STTH30R04G	D <sup>2</sup> PAK	1.48 g	1000	Tape and reel
STTH30R04W	STTH30R04W	DO-247	4.40 g	30	Tube
STTH30R04PI	STTH30R04PI	DOP3I	4.46 g	30	Tube

# 4 Revision history

Date	Revision	Description of Changes
31-Mar-2007	1	First issue.

#### Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2007 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

477